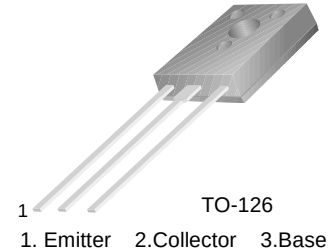


BM13003

High Voltage Switch Mode Applications

- High Speed Switching
- Suitable for Switching Regulator and Motor Control



NPN Silicon Transistor

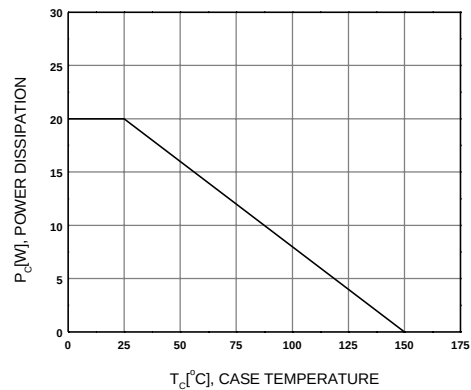
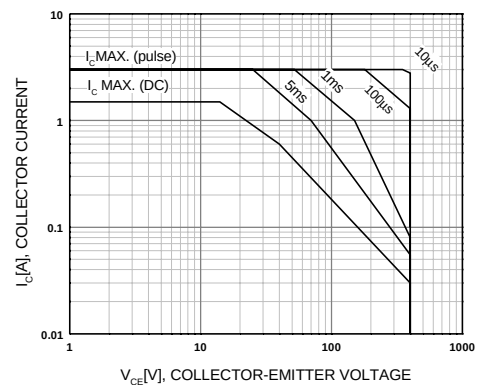
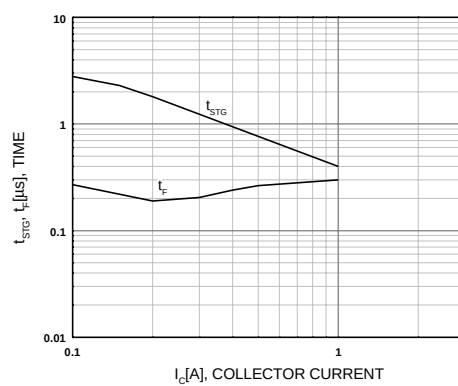
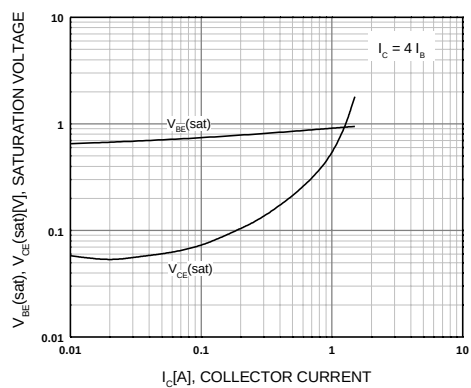
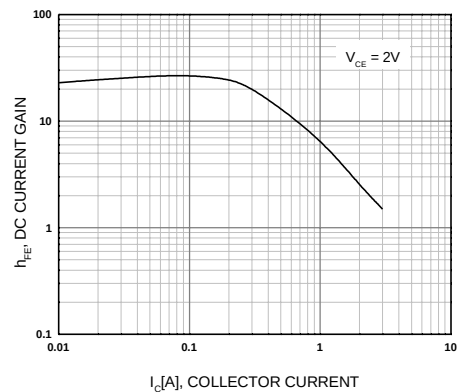
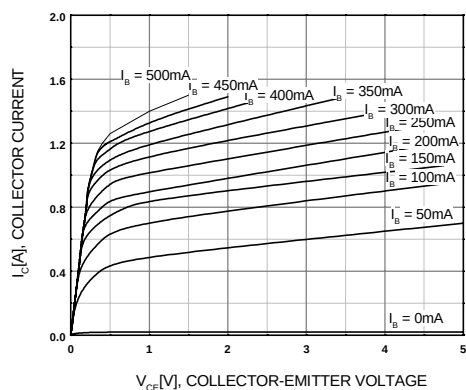
Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	650	V
V_{CEO}	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current (DC)	1.5	A
I_{CP}	Collector Current (Pulse)	3	A
I_B	Base Current	0.75	A
P_C	Collector Dissipation ($T_C=25^{\circ}\text{C}$)	20	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^{\circ}\text{C}$

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	400			V
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 9\text{V}, I_C = 0$			10	μA
h_{FE}	*DC Current Gain	$V_{CE} = 2\text{V}, I_C = 0.5\text{A}$ $V_{CE} = 2\text{V}, I_C = 1\text{A}$	30 25		40	
$V_{CE(sat)}$	*Collector Emitter Saturation Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$ $I_C = 1\text{A}, I_B = 0.25\text{A}$ $I_C = 1.5\text{A}, I_B = 0.5\text{A}$			0.5 1 3	V V V
$V_{BE(sat)}$	*Base Emitter Saturation Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$ $I_C = 1\text{A}, I_B = 0.25\text{A}$			1 1.2	V V
C_{ob}	Output Capacitance	$V_{CB} = 10\text{V}, f = 0.1\text{MHz}$		21		pF
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 0.1\text{A}$	4			MHz
t_{ON}	Turn On Time	$V_{CC} = 125\text{V}, I_C = 1\text{A}$ $I_{B1} = 0.2\text{A}, I_{B2} = -0.2\text{A}$ $R_L = 125\Omega$			1.1	μs
t_{STG}	Storage Time				4.0	μs
t_F	Fall Time				0.7	μs

* Pulse Test: Pulse Width=5ms, Duty Cycle≤10%



Package Dimensions (mm)

TO-126

